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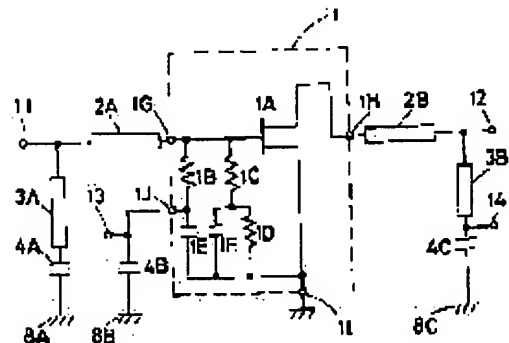
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## (54) MICROWAVE INTEGRATED CIRCUIT ELEMENT

## (57)Abstract:

PURPOSE: To facilitate a manufacture of a microwave integrated circuit by reducing the number of chip components such as a field effect transistor to be mounted on a substrate of high permittivity.

CONSTITUTION: A field effect transistor(FET) 1A is formed on a semiconductor substrate and resistance elements 1B and 1C are formed on the semiconductor substrate in a state wherein one end of each element is connected to the gate of the FET 1A. A capacitance element 1E is formed on the semiconductor substrate in a state wherein one end of this element is connected to the other end of the resistance element 1B and the other end thereof to the source of the FET 1A, while a resistance element 1D and a capacitance element 1F are formed on the semiconductor substrate in a state wherein one end of each of these elements is connected to the other end of the resistance element 1C and the other end thereof to the source of the FET 1A.



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